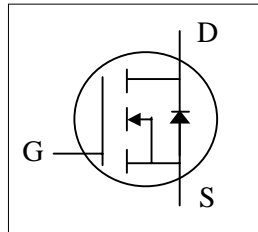




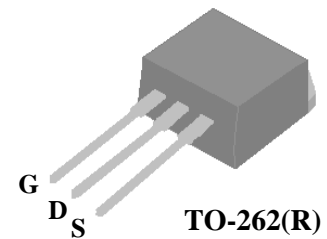
- ▼ Low Gate Charge
- ▼ Single Drive Requirement
- ▼ RoHS Compliant



BV_{DSS}	60V
$R_{DS(ON)}$	18m Ω
I_D	60A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	+25	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	60	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	38	A
I_{DM}	Pulsed Drain Current ¹	230	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	89	W
	Linear Derating Factor	0.7	W/ $^\circ C$
E_{AS}	Single Pulse Avalanche Energy ³	45	mJ
I_{AR}	Avalanche Current ³	30	A
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	1.4	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	$^\circ C/W$



Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =1mA	-	0.06	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =35A	-	-	18	mΩ
		V _{GS} =4.5V, I _D =25A	-	-	22	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	-	3	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =35A	-	55	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =60V, V _{GS} =0V	-	-	10	uA
	Drain-Source Leakage Current (T _j =125°C)	V _{DS} =48V, V _{GS} =0V	-	-	250	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =35A	-	32	51	nC
Q _{gs}	Gate-Source Charge	V _{DS} =48V	-	8	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	20	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =30V	-	11	-	ns
t _r	Rise Time	I _D =35A	-	58	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =10V	-	45	-	ns
t _f	Fall Time	R _D =0.86Ω	-	80	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	3170	5070	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	280	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	230	-	pF
R _g	Gate Resistance	f=1.0MHz	-	1.7	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =35A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time ²	I _S =35A, V _{GS} =0V,	-	50	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs	-	48	-	nC

Notes:

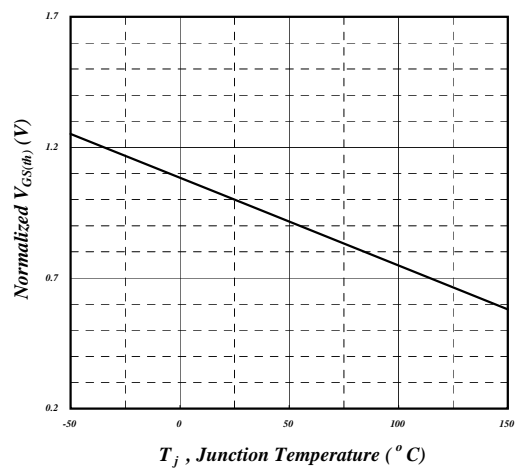
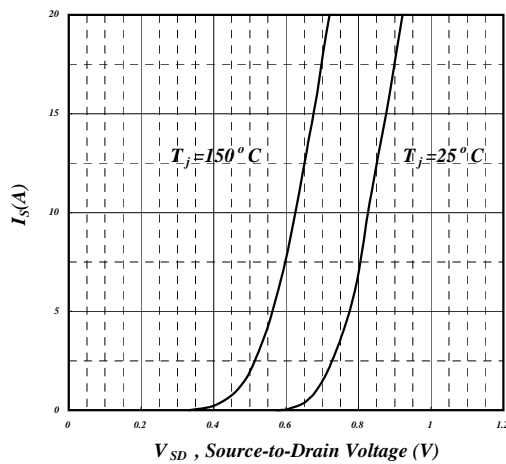
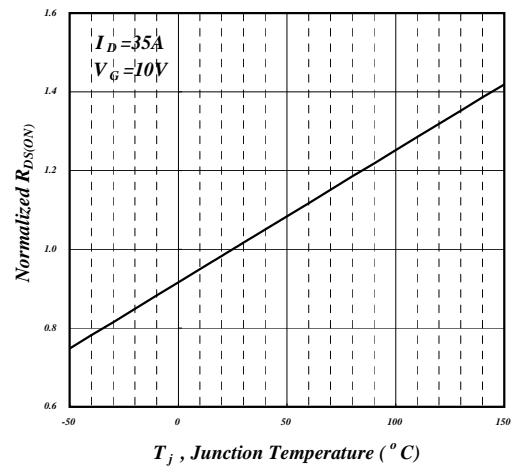
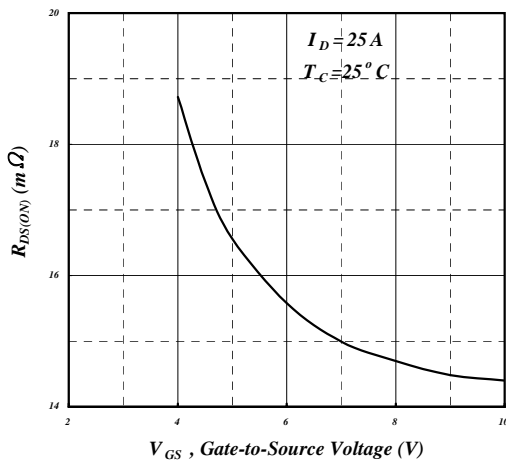
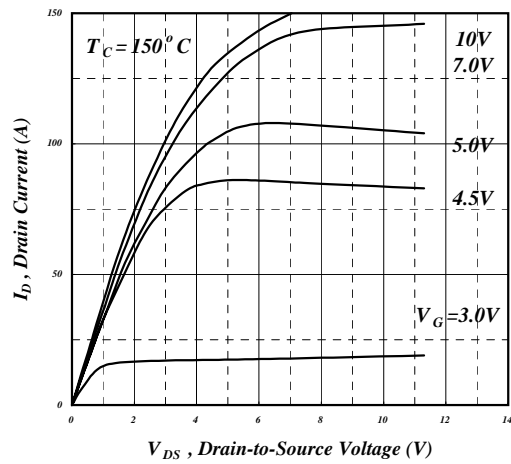
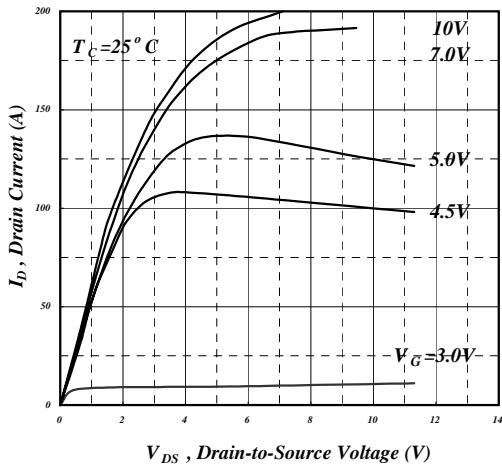
- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Starting T_j=25°C, V_{DD}=30V, L=100uH, R_G=25Ω, I_{AS}=30A.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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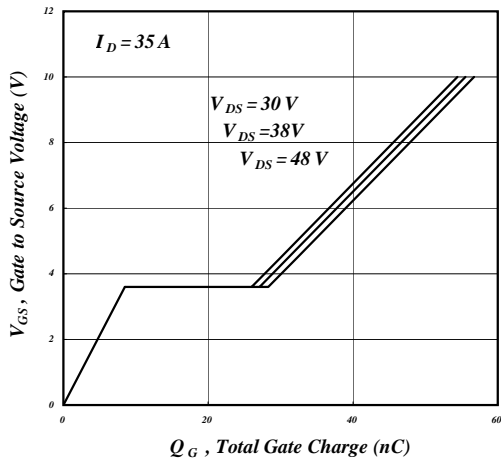


Fig 7. Gate Charge Characteristics

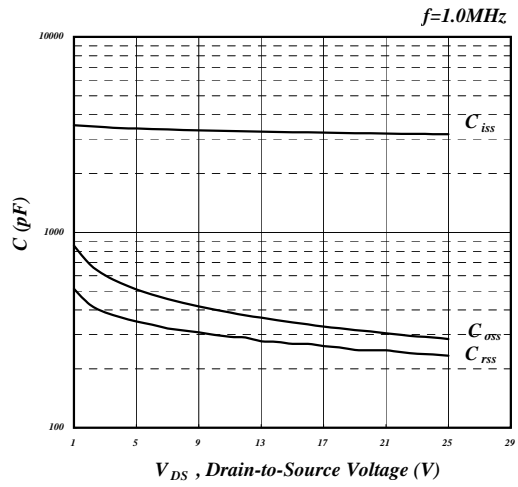


Fig 8. Typical Capacitance Characteristics

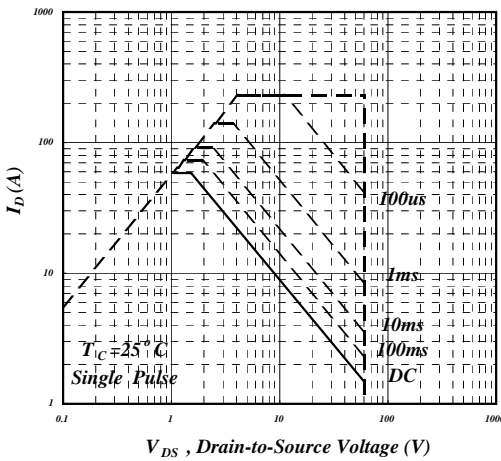


Fig 9. Maximum Safe Operating Area

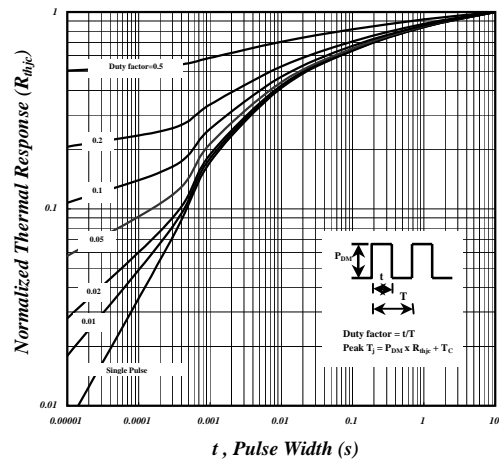


Fig 10. Effective Transient Thermal Impedance

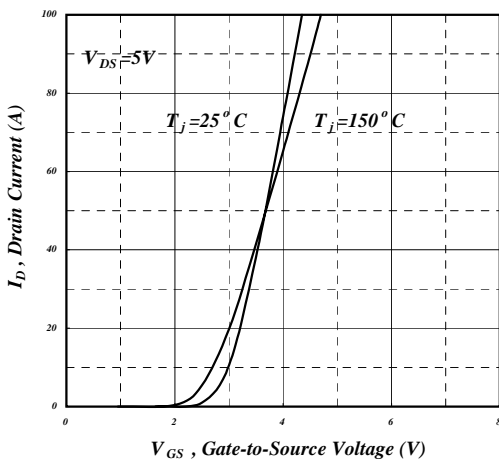


Fig 11. Transfer Characteristics

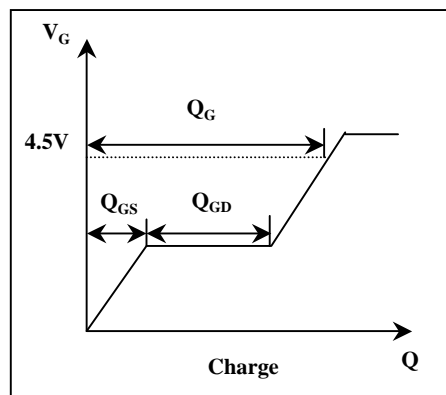


Fig 12. Gate Charge Waveform